
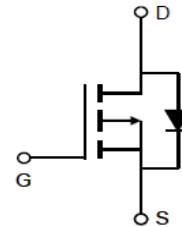
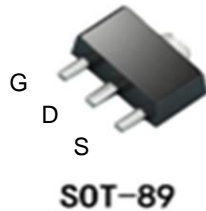


**100V P-Channel Trench MOSFET(Preliminary)**

<p><b>General Description</b></p> <ul style="list-style-type: none"> <li>● Trench Power technology</li> <li>● Low <math>R_{DS(ON)}</math></li> <li>● Low Gate Charge</li> <li>● Optimized for fast-switching applications</li> </ul> <p><b>Applications</b></p> <ul style="list-style-type: none"> <li>● Synchronous Rectification in DC/DC and AC/DC Converters</li> <li>● Isolated DC/DC Converters in Telecom and Industrial</li> </ul>	<p><b>Product Summary</b></p> <table> <tr> <td><math>V_{DS}</math></td> <td>-100V</td> </tr> <tr> <td><math>I_D</math> (at <math>V_{GS}=-10V</math>)</td> <td>-1.5A</td> </tr> <tr> <td><math>R_{DS(ON)}</math> (at <math>V_{GS}=-10V</math>)</td> <td>&lt; 1.54<math>\Omega</math></td> </tr> <tr> <td><math>R_{DS(ON)}</math> (at <math>V_{GS}=-4.5V</math>)</td> <td>&lt; 1.66<math>\Omega</math></td> </tr> </table> <p>100% UIS Tested</p> 	$V_{DS}$	-100V	$I_D$ (at $V_{GS}=-10V$ )	-1.5A	$R_{DS(ON)}$ (at $V_{GS}=-10V$ )	< 1.54 $\Omega$	$R_{DS(ON)}$ (at $V_{GS}=-4.5V$ )	< 1.66 $\Omega$
$V_{DS}$	-100V								
$I_D$ (at $V_{GS}=-10V$ )	-1.5A								
$R_{DS(ON)}$ (at $V_{GS}=-10V$ )	< 1.54 $\Omega$								
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$ )	< 1.66 $\Omega$								

SOT-89



Part Number	Package Type	Form	Marking
TTM01P10ATS	SOT-89	Tape&Reel	01P10AT

**Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	- 100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>B</sup>	$I_D$	$T_C = 25^\circ\text{C}$	-1.5
		$T_C = 100^\circ\text{C}$	-0.7
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	-4.5	A
Avalanche Current <sup>A</sup>	$I_{AS}$	-2	A
Single Pulse Avalanche Energy $L = 0.3\text{mH}$ <sup>A</sup>	$E_{AS}$	0.8	mJ
Power Dissipation <sup>C</sup>	$P_D$	$T_C = 25^\circ\text{C}$	1.5
		$T_C = 100^\circ\text{C}$	1.25
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 175	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Case	Steady-State $R_{\theta JC}$	20	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient	Steady-State $R_{\theta JA}$	100	



Electrical Characteristics( $T_J = 25^\circ\text{C}$ unless otherwise noted)						
Symbol	Parameter	Conditions	Value			Units
			Min	Typ	Max	
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$	-100			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -100\text{V}, V_{GS} = 0\text{V}$	$T_J = 25^\circ\text{C}$		-1	$\mu\text{A}$
			$T_J = 100^\circ\text{C}$		-100	
$I_{GSS}$	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-1	-1.7	-2.4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{V}, I_D = -1\text{A}$		1.29	1.54	$\Omega$
		$V_{GS} = -4.5\text{V}, I_D = -1\text{A}$		1.43	1.66	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = -5\text{V}, I_D = -1.5\text{A}$		0.24		S
$V_{SD}$	Diode Forward Voltage	$I_S = -1.5\text{A}, V_{GS} = 0\text{V}$			-1	V
$I_S$	Maximum Body-Diode Continuous Current <sup>B</sup>				-1.5	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = -50\text{V}, f = 1\text{MHz}$		210		$\text{pF}$
$C_{oss}$	Output Capacitance			17		
$C_{rss}$	Reverse Transfer Capacitance			5		
<b>SWITCHING PARAMETERS</b>						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS} = -10\text{V}, V_{DS} = -80\text{V}, I_D = -1\text{A}$		25		nC
$Q_{gs}$	Gate Source Charge			3		
$Q_{gd}$	Gate Drain Charge			7		
$t_{D(on)}$	Turn-On Delay Time	$V_{GS} = -10\text{V}, V_{DS} = -80\text{V}, I_D = -1\text{A}, R_G = 2.5\Omega$		8		ns
$t_r$	Turn-On Rise Time			4		
$T_{D(off)}$	Turn-Off Delay Time			32		
$t_f$	Turn-Off Fall Time			7		
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F = -1\text{A}, di/dt = 100\text{A}/\mu\text{s}$		25		ns
$Q_{rr}$	Body Diode Reverse Recovery Charge			31		nC

A. Single pulse width limited by maximum junction temperature.

B. The maximum current rating is package limited.

C. The power dissipation  $P_D$  is based on  $T_{J(MAX)} = 175^\circ\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

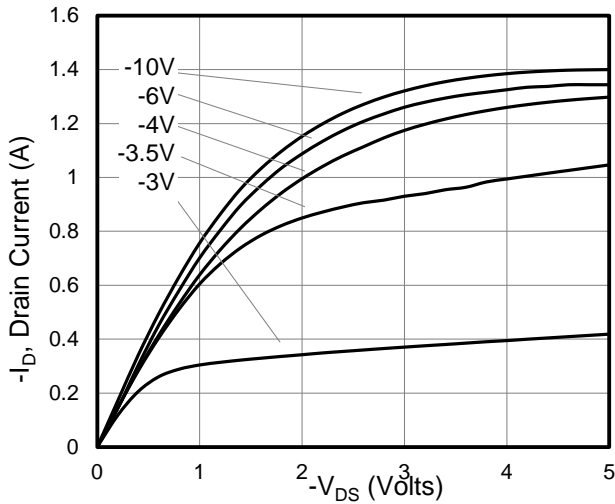


Figure 1: On-Region Characteristics

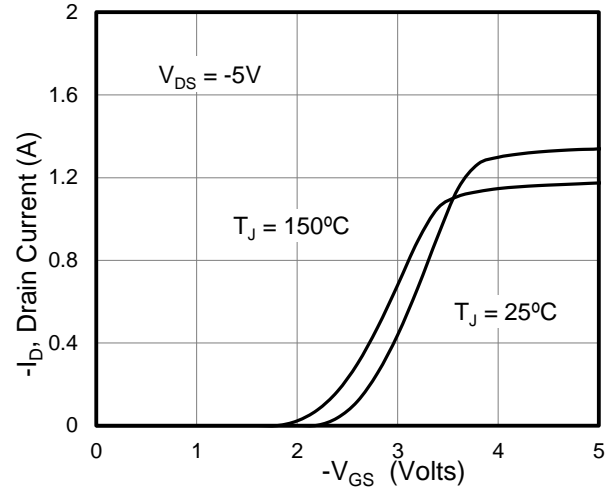


Figure 2: Transfer Characteristics

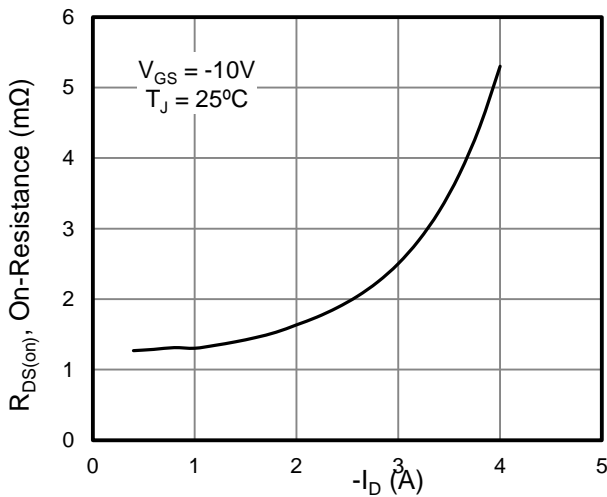


Figure 3: On-Resistance vs. Drain Current

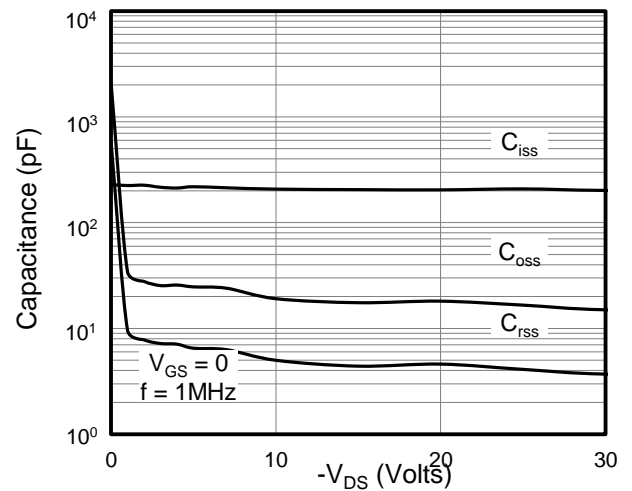


Figure 4: Capacitance Characteristics

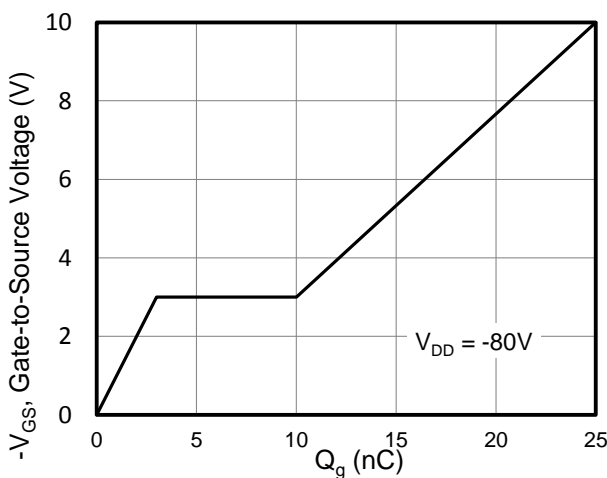


Figure 5: Gate Charge Characteristics

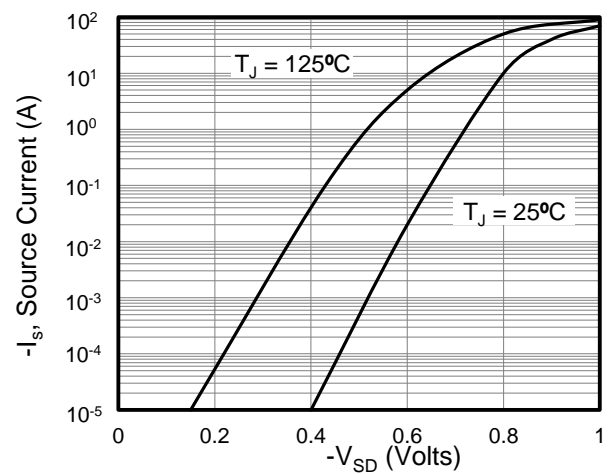


Figure 6: Body Diode Forward Voltage



Typical Characteristics  $T_J = 25^{\circ}\text{C}$ , unless otherwise noted

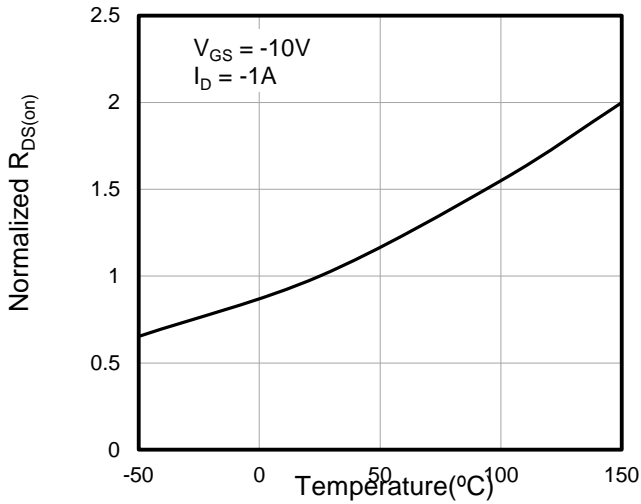


Figure 7: On-Resistance vs. Junction Temperature

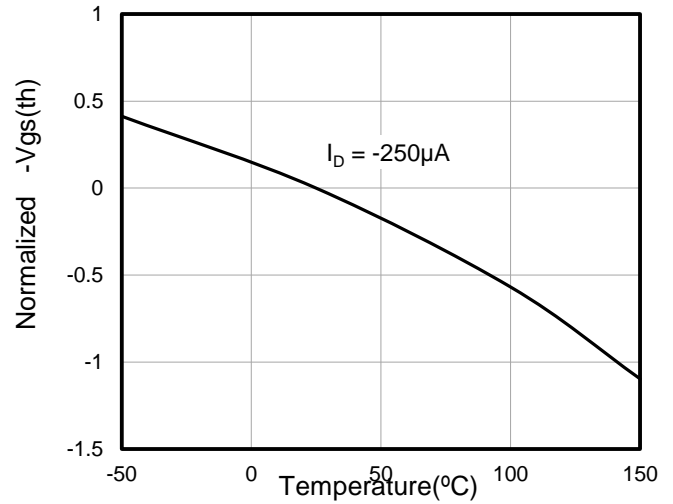


Figure 8:  $V_{gs(th)}$  vs. Junction Temperature

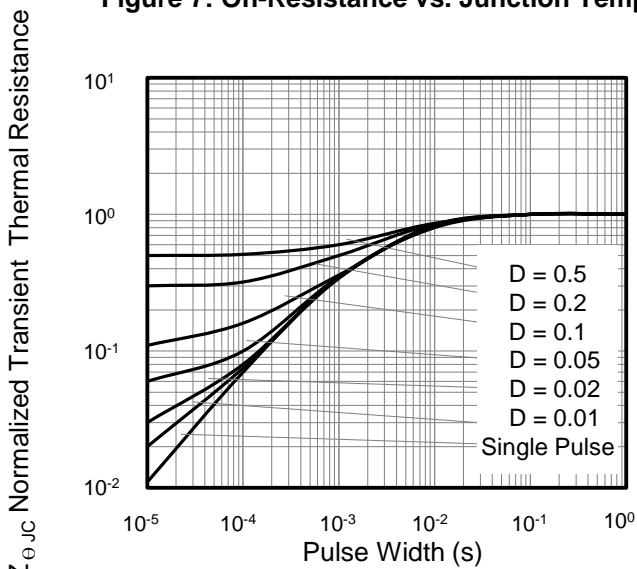


Figure 11: Normalized Transient Thermal Resistance

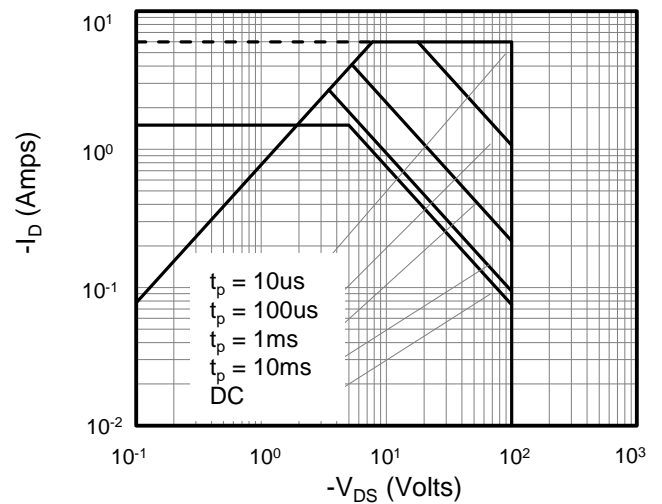


Figure 12: Safe Operating Area



Figure A: Gate Charge Test Circuit and Waveform

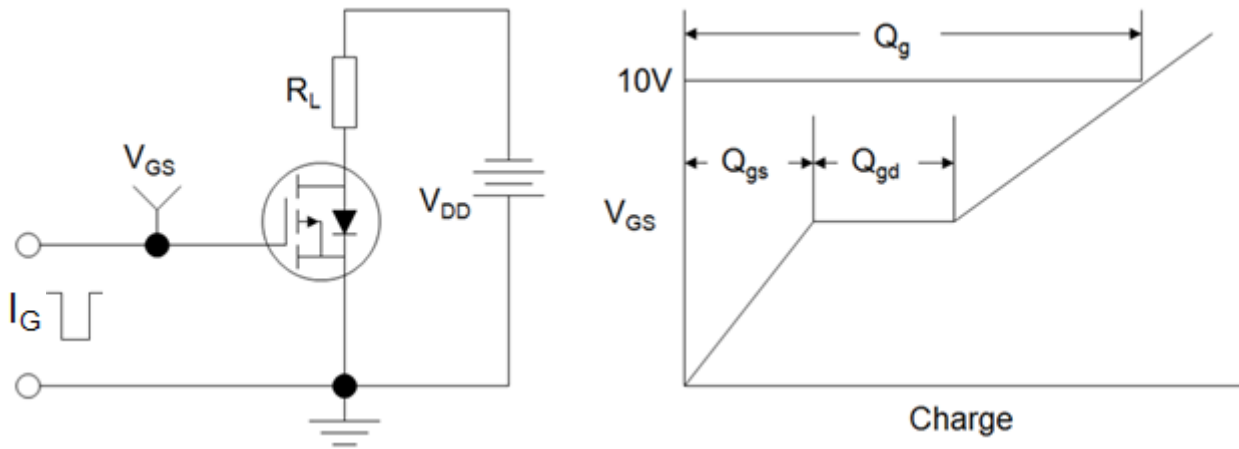


Figure B: Resistive Switching Test Circuit and Waveform

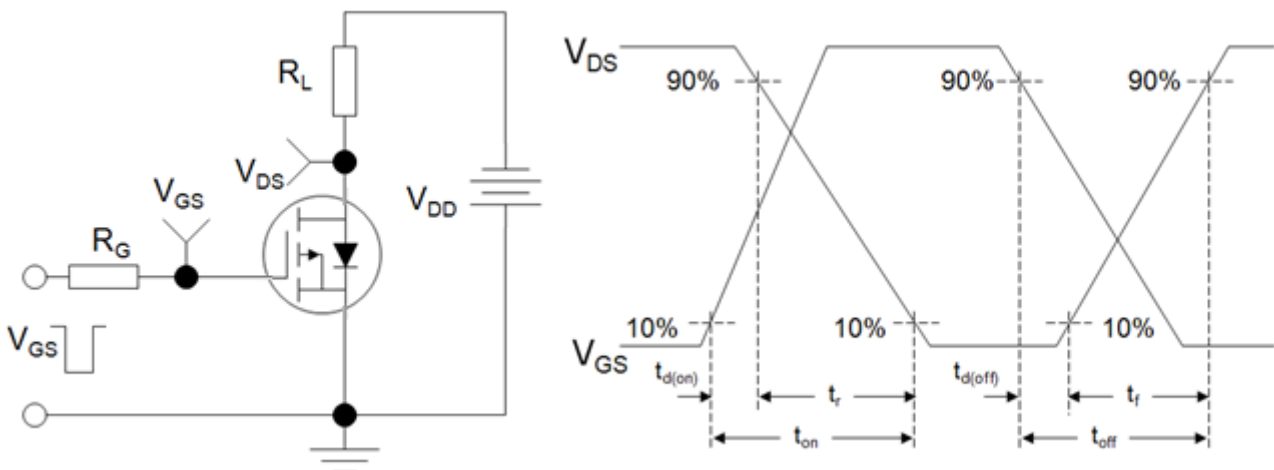
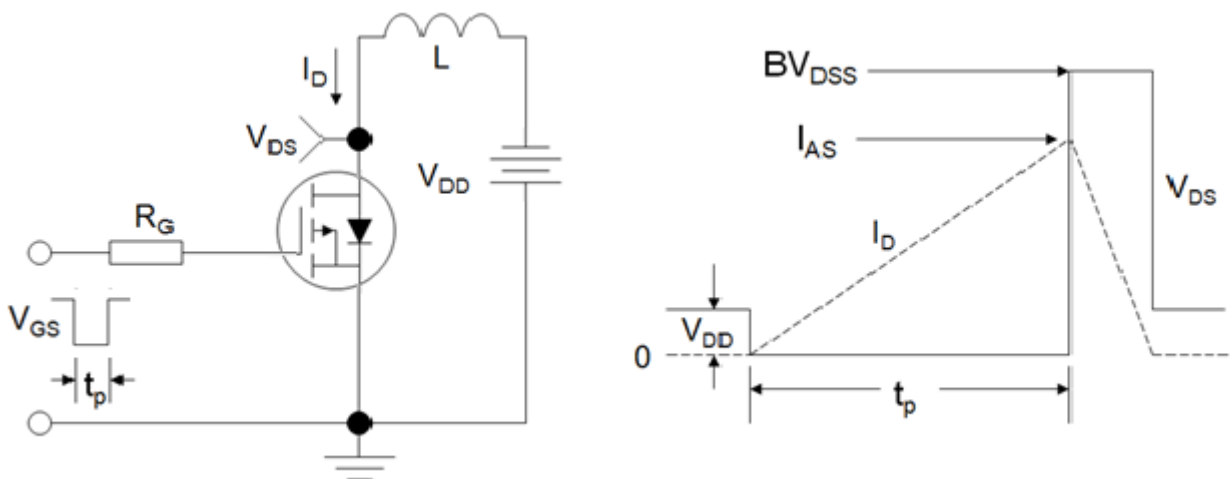
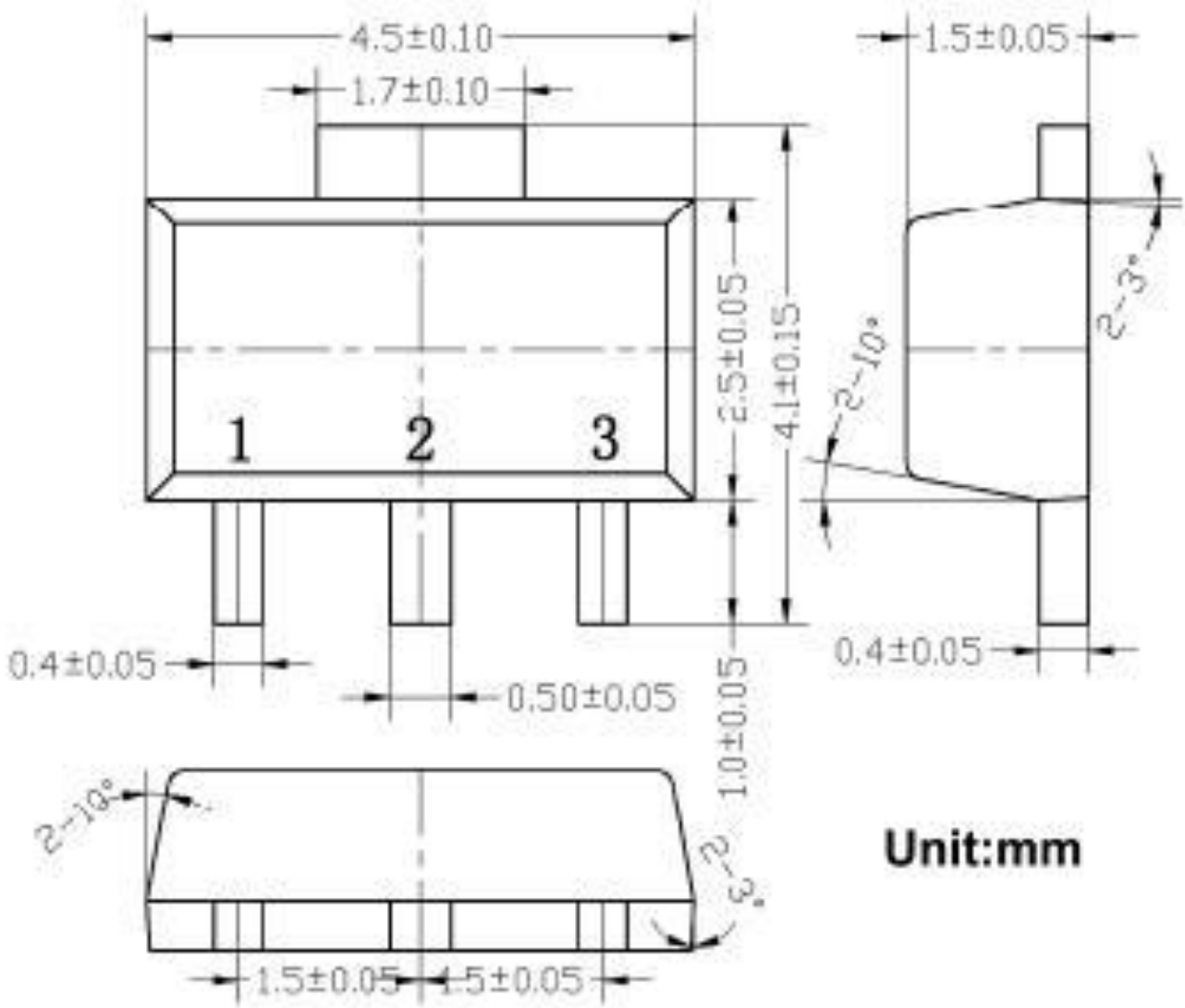


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





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